2SB1399

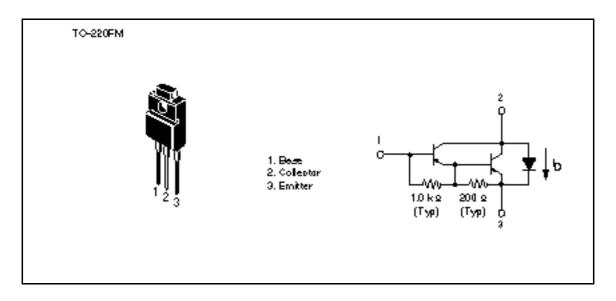
Silicon PNP Triple Diffused

HITACHI

Application

Low frequency power amplifier

Outline





2SB1399

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	-120	V	
Collector to emitter voltage	V _{CEO}	-120	V	
Emitter to base voltage	V_{EBO}	- 7	V	
Collector current	I _c	-10	Α	
Collector peak current	C (peak)	– 15	Α	
Collector power dissipation	P _c	2	W	
	P _c *1	30		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
C to E diode forward current	I _D *1	10	Α	

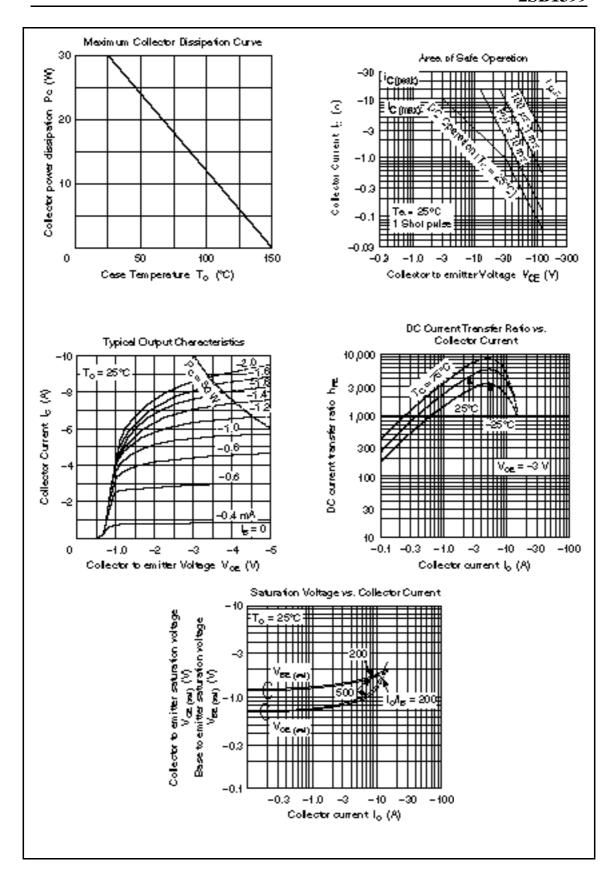
Note: 1. Value at $T_c = 25$ °C.

Electrical Characteristics ($Ta = 25^{\circ}C$)

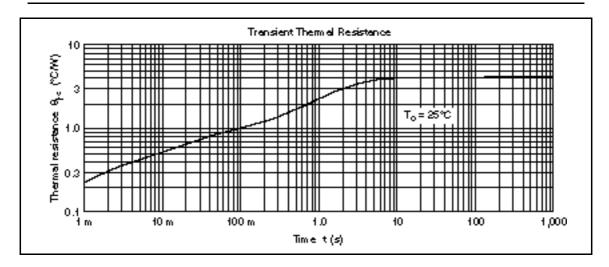
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	_	_	V	$I_{c} = -0.1 \text{ mA}, I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{\rm C}$ = -25 mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 7	_	_	V	$I_{\rm E} = -50 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	-10	μΑ	$V_{CB} = -100 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	-10		$V_{CE} = -100 \text{ V}, R_{BE} =$
DC current transfer ratio	h _{FE}	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -5 \text{ A}^{*1}$
Collector to emitter saturation	V _{CE (sat)1}	_	_	-1.5	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	V _{CE (sat)2}	_	_	-3.0	_"	$I_{\rm C} = -10 \text{ A}, I_{\rm B} = -100 \text{ mA}^{*1}$
Base to emitter saturation	V _{BE (sat)1}	_	_	-2.0	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	V _{BE (sat)2}	_	_	-3.5	_'	$I_C = -10 \text{ A}, I_B = -100 \text{ mA}^{*1}$
C to E diode forward voltage	$V_{\scriptscriptstyle D}$	_	_	3.0	V	I _D = 10 A*1

Note: 1. Pulse Test.

See switching characteristic curve of 2SB955(K).



2SB1399



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IITACHI

Hitachi, Ltd. Semiconductor & IC DV. Nippon Bidg., 2-5-2, Ohte-medif, Chiyoda-ku, Tokyo 100, Japan Tet Tokyo (03) 3270-2111 Fex: (03) 3270-5109

For further in forme I on write to:

Hitechi Americe, Ltd. Semiconductor & IC Div. 2000 Sierre Point Perkwey Brisbane, CA. 94005-4835 USA

Tet +15-589-8300 Fex: 415-583-4207

Hitechi Burope GmbH Bedronic Components Group Carbinertal Burope Darneicher Streiße 3 D-85622 Feldkirchen München Tet 089-9 94 80-0 Fex: 089-9-29-30-00

Hitachi Burope Ltd. Bledronic Components DV. Nothern Burgoe Headquarters Whilebrook Park Lower Cook fem Road Maidenhead Borkehire SL68YA United Kingdom Tet 0628-585000 Fex: 0628-778322

Hitechi Asie Pte. Ltd. #5 Collyer Quey #20-00 Hitachi Tower Snapore 0104 Tet 535-2400 Fex: 535-1533

Hitechi Asia (Hong Kong) Ltd. Unit 706, North Tower, World Firence Centre Herbour City, Certon Road Teim She Teui, Kowloon Hang Kong Tet 27359248 Fex: 27306074